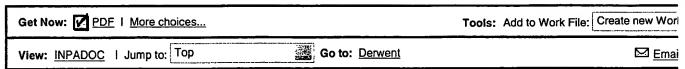
## TEST AVAILABLE COPY



## The Delphion Integrated View



Title: JP61224423A2: REACTIVE ION ETCHING APPRATUS

Reactive ion etching device - includes material around the wafer being Propert Title:

etched which can reduce the quantity of etching speeds at the same rate

as the wafer [Derwent Record]

JP Japan 

®Kind:

KATSURA TOSHIHIKO;

ABE MASAYASU: TAKAOKI KIYOSHI; **AOYAMA MASAHARU:** 

**TOSHIBA CORP** 

News, Profiles, Stocks and More about this company

Published / Filed: 1986-10-06 / 1985-03-29

> **₽**Application JP1985000065407

Number:

♥IPC Code: H01L 21/302;

Priority Number: 1985-03-29 JP1985000065407

> PURPOSE: To enable the wafer surface to be etched by a **P**Abstract: method wheein a material to reduce the etching species of reactive

> > gas in the ratio almost the

CONSTITUTION: The faciang of an electrode 6 and an insulating

sheet 10 are made larger than the outside diameter of a

semiconductor 8 which a correcting ring 20 is provided between a step difference 12 due to the facing and the semi conductor wafer 8. Any material abel to reduce etching species of reactive gas in the ratio subject to the difference between the etched materials but at least almost the same as that of any etched materials is applicable to the correcting ring 20. In such a constitution, there is a material to reduce the etching element in the peripheral part of semiconductor wafer as well as on the semiconductor wafer therefore tha apart subject to uneven concentration of etching species (a) can be shifted to outside making the concentration of etching even on the semiconductor wafer 8. Resultantly, the semiconductor wafer 8 can be etched evenly.

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None Get Now: Family Legal Status Report

Legal Status:

**Family**: Show 6 known family members

& Forward Go to Result Set: Forward references (7)



## References:

PDF	Patent	Pub.Date	Inventor	Assignee	Title
23	<u>US6184150</u>	2001-02-06	Yang; Chan- Lon	Applied Materials Inc.	Oxide etch process with selectivity to nitride suite on surfaces of uneven
<b>88</b>	<u>US6171974</u>	2001-01-09	Marks; Jeffrey	Applied Materials, Inc.	High selectivity oxide e for integrated circuit str
器	<u>US5951814</u>	1999-09-14	Saito; Kazuo	Nisshinbo Industries, Inc.	Electrode for plasma et
2	<u>US5681419</u>	1997-10-28	Yoon; Hak- Soon	Hyundai Electronics Industries Co., Ltd.	Reactive ion etching ar
器	<u>US5556500</u>	1996-09-17	Hasegawa; Makoto	Tokyo Electron Limited	Plasma etching appara
Æ	<u>US5330607</u>	1994-07-19	Nowicki; Ronald S.	Genus, Inc.	Sacrificial metal etchba
<b>23</b>	<u>US5292399</u>	1994-03-08	Lee; Terrance Y.	Applied Materials, Inc.	Plasma etching appara conductive means for in arcing

♥Other Abstract Info: DERABS C86-302121 DERC86-302121

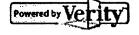








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